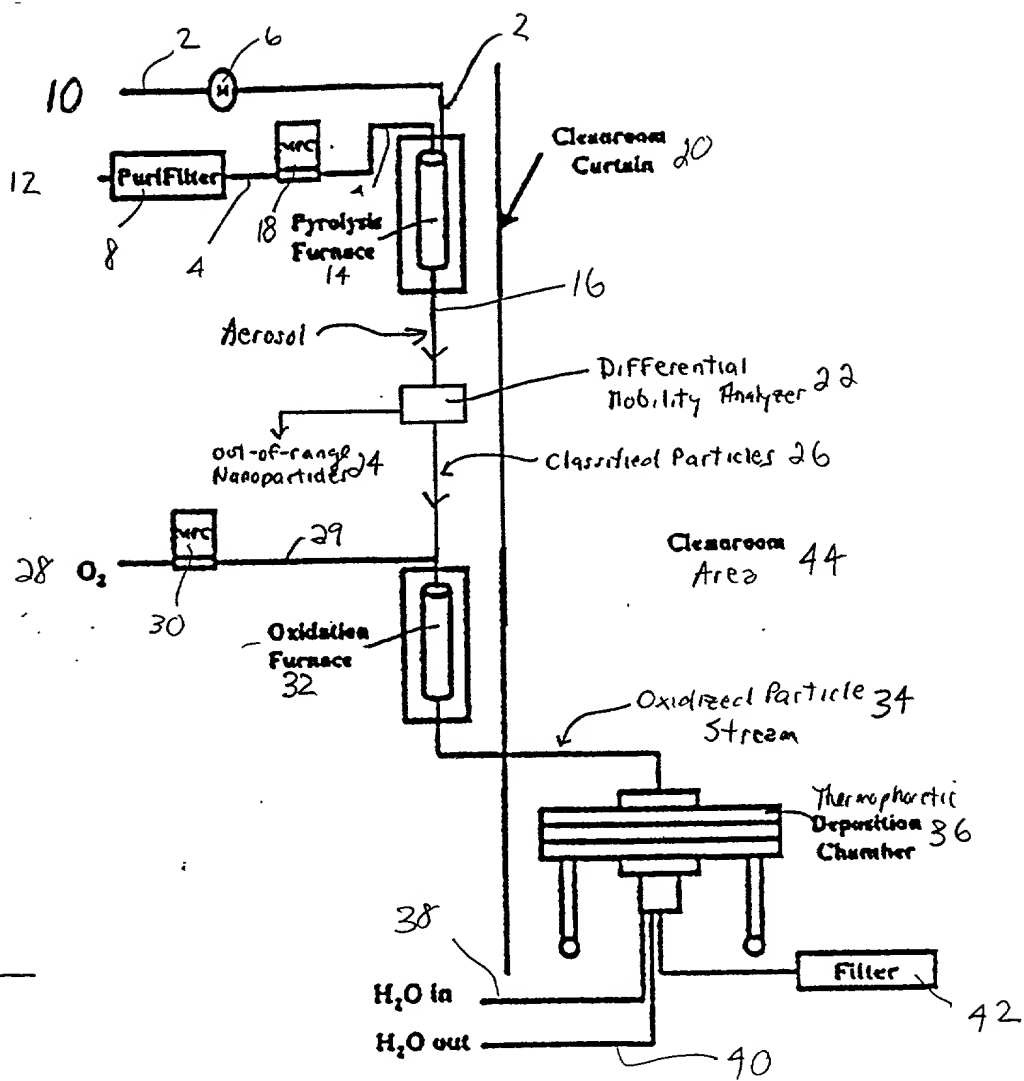


FIGURE 1

FIGURE 2



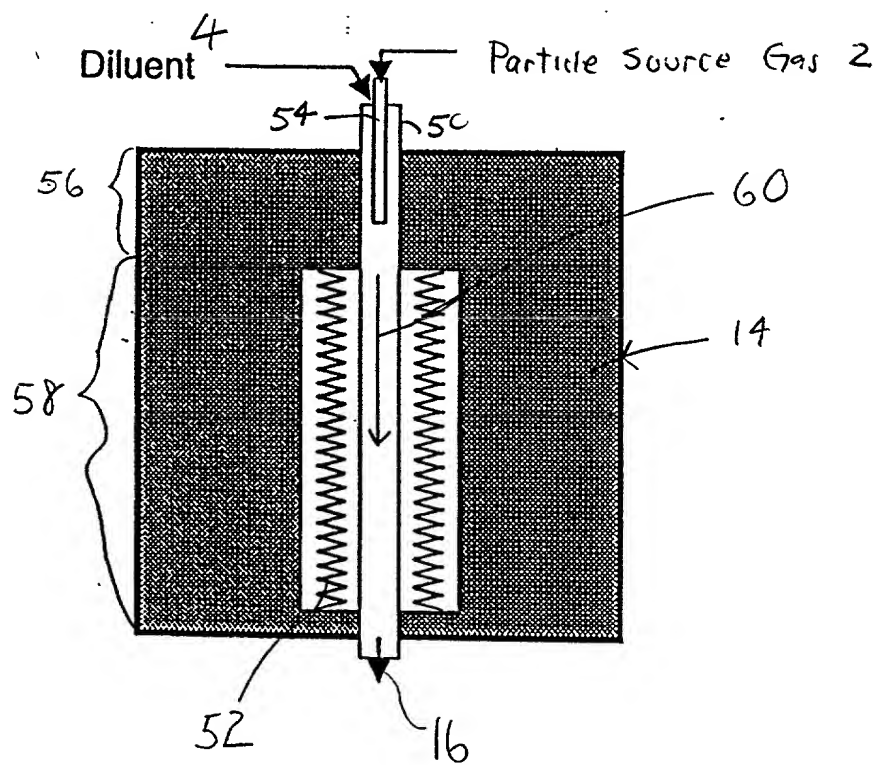


FIGURE 3

TOP SECRET 1625660

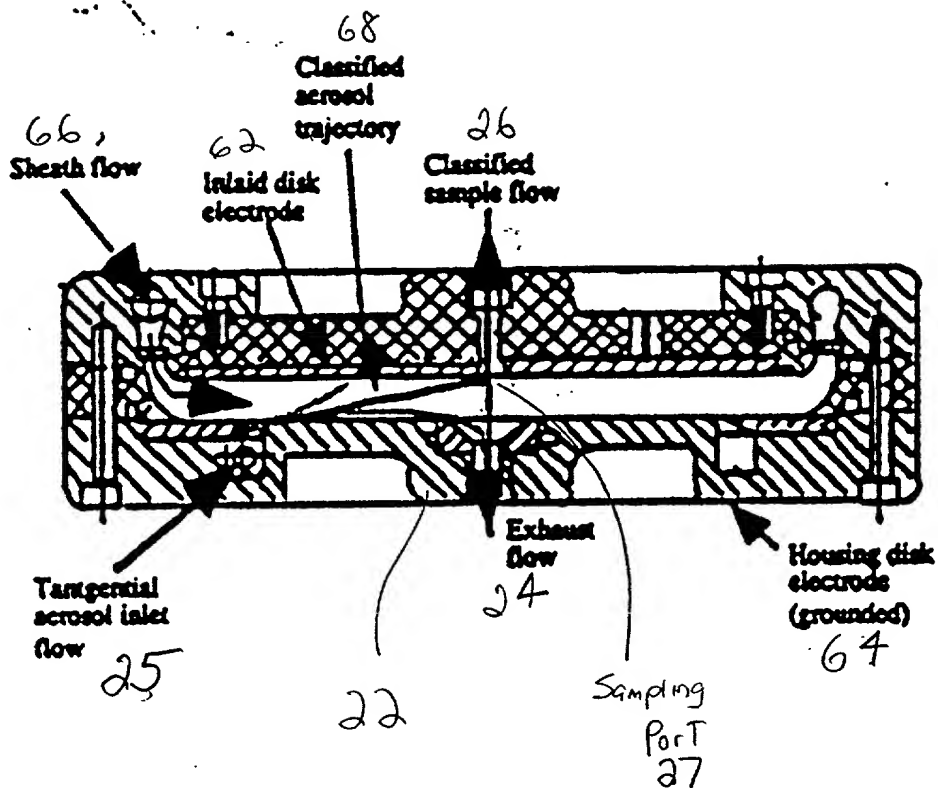


FIGURE 4

TOP SECRET

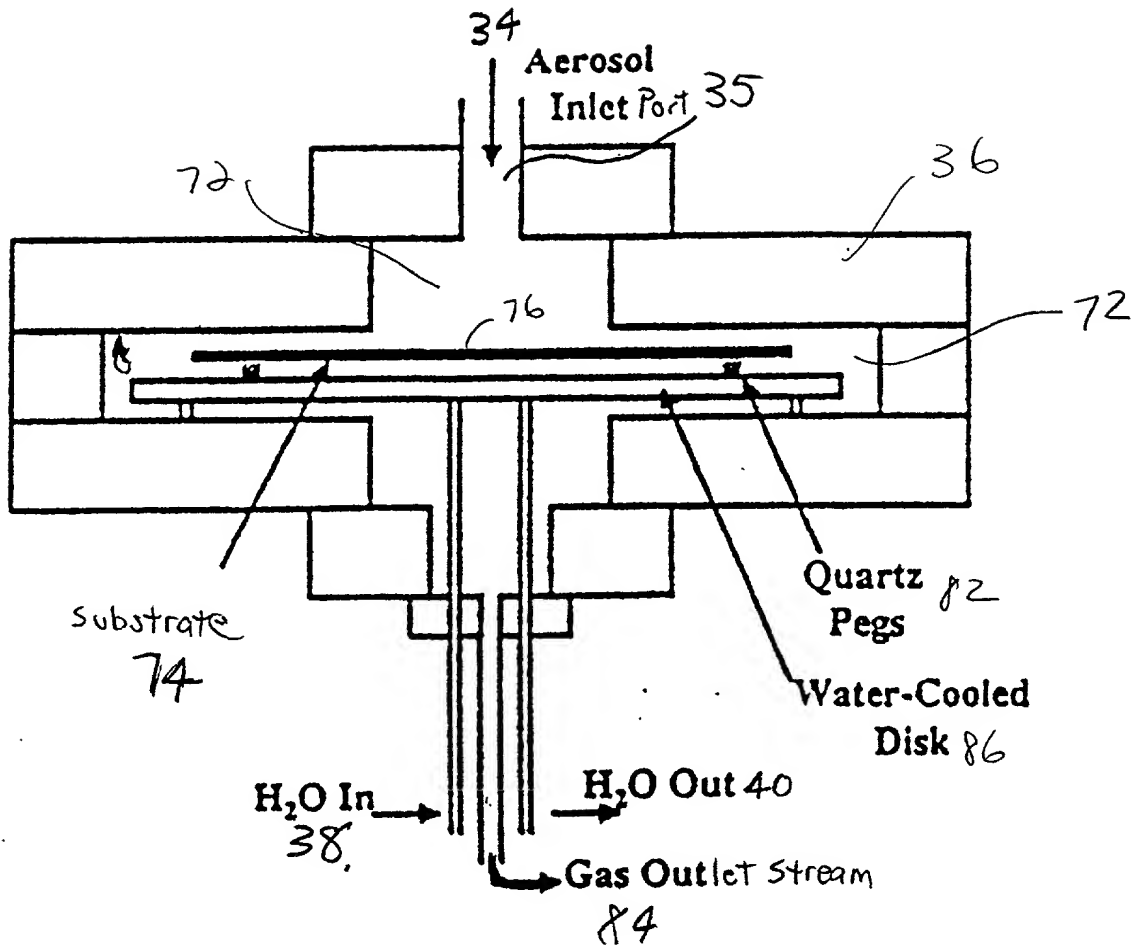


FIGURE 5

FIGURE 6

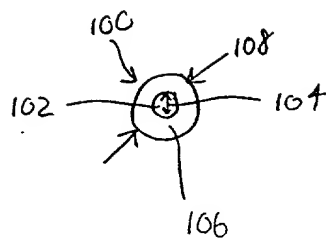


FIGURE 7

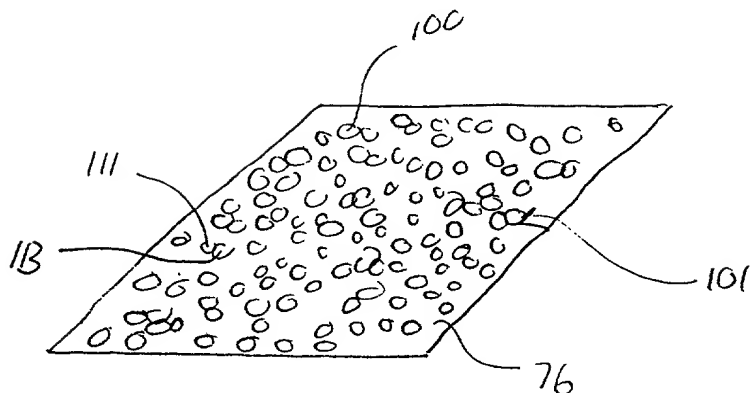


FIGURE 8

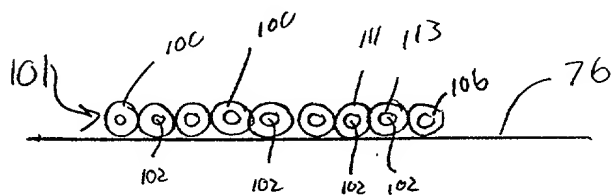


FIGURE 10

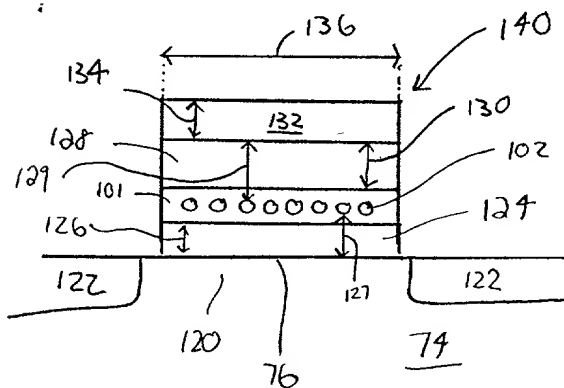


FIGURE 9

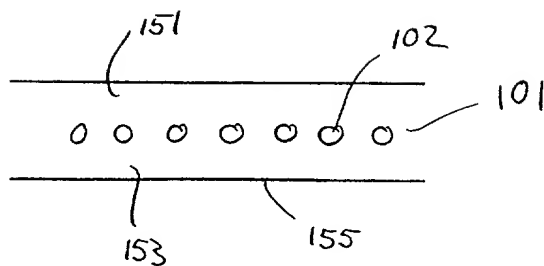
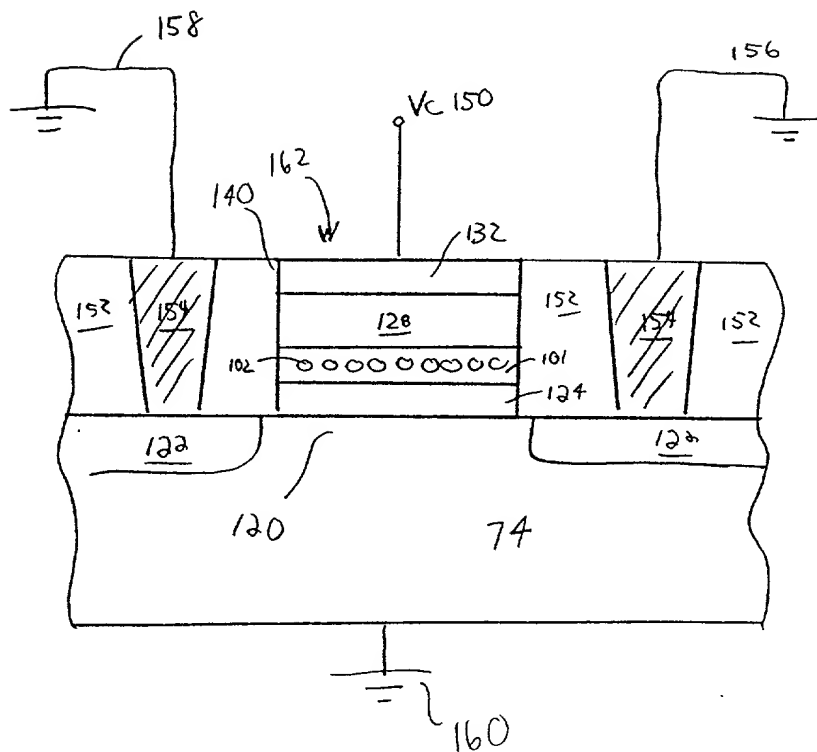


FIGURE 11



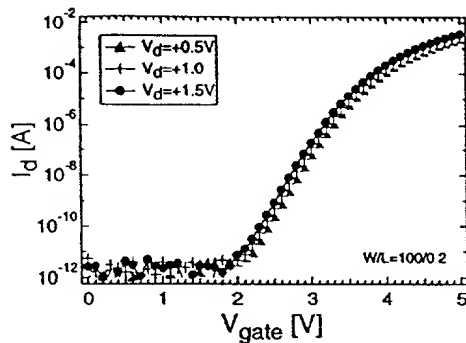


Fig 12 ... Subthreshold characteristics of a 0.2μm n-type aerosol-nanocrystal floating-gate MOSFET (subthreshold slope = 200mV/dec; DIBL = 100mV/V).

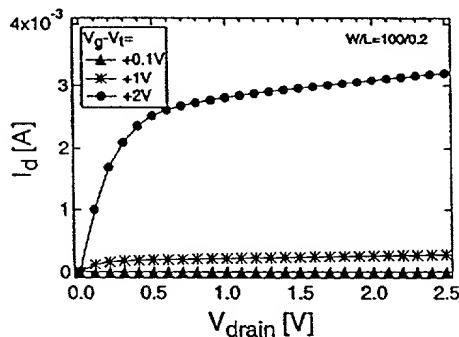


Fig 13 Output characteristics of a 0.2μm aerosol-nanocrystal floating-gate MOSFET; drive current = 30μA/μm.

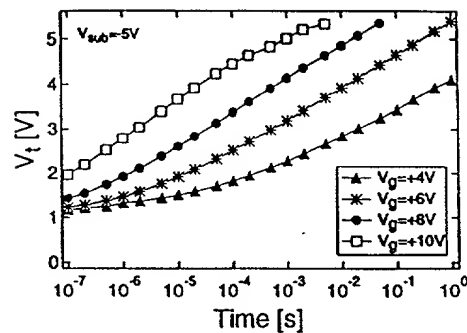


Fig 14: Programming transients (uniform FN tunneling) of the nanocrystal NVM device.

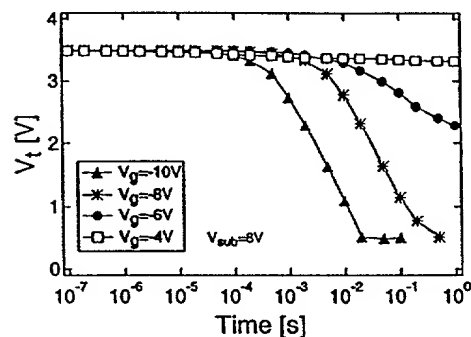


Fig 15 Erase transients (uniform FN tunneling).

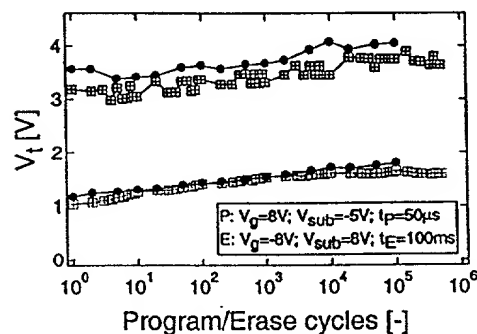


Fig 16 : Endurance characteristic; only limited window closure is observed after 10<sup>5</sup> program/erase cycles.



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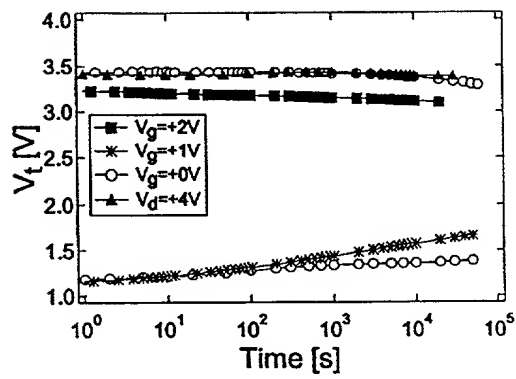


FIGURE 17